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## FQN1N50C N-Channel QFET<sup>®</sup> MOSFET

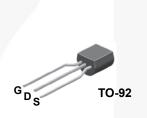
### 500 V, 0.38 A, 6 $\Omega$

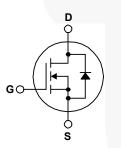
#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- 0.38 A, 500 V,  $R_{DS(on)}$  = 6  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 0.19 A
- Low Gate Charge (Typ. 4.9 nC)
- Low Crss (Typ. 4.1 pF)
- 100% Avalanche Tested





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

| Symbol                            | Parameter  |                                       |          | FQN1N50CTA  | Unit |  |
|-----------------------------------|--|---------------------------------------|----------|-------------|------|--|
| V <sub>DSS</sub>                  | Drain-Source Voltage   |                                       | 500      |             | V    |  |
| ID                                | Drain Current  | - Continuous (T <sub>C</sub> = 25°C)  |          | 0.38        | A    |  |
|                                   |  | - Continuous (T <sub>C</sub> = 100°C) |          | 0.24        | A    |  |
| I <sub>DM</sub>                   | Drain Current - Pulsed (Note 1)  |                                       | (Note 1) | 3.04        | A    |  |
| V <sub>GSS</sub>                  | Gate-Source Voltage  |                                       |          | ± 30        | V    |  |
| E <sub>AS</sub>                   | Single Pulsed Avalanche Energy (Note 2)                                  |                                       | (Note 2) | 44.4        | mJ   |  |
| I <sub>AR</sub>                   | Avalanche Current  |                                       | (Note 1) | 0.38        | А    |  |
| E <sub>AR</sub>                   | Repetitive Avalanche Energy  |                                       | (Note 1) | 0.21        | mJ   |  |
| dv/dt                             | Peak Diode Recovery dv/dt (N   |                                       | (Note 3) | 4.5         | V/ns |  |
| P <sub>D</sub>                    | Power Dissipation ( $T_A = 25^{\circ}C$ )                                |                                       |          | 0.89        | W    |  |
|                                   | Power Dissipation (T <sub>L</sub> = 25°C)                                |                                       |          | 2.08        | W    |  |
|                                   | - Derate above 25°C  |                                       |          | 0.017       | W/°C |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                                  |                                       |          | -55 to +150 | °C   |  |
| TL                                | Maximum Lead Temperature for Soldering,<br>1/8" from Case for 5 Seconds. |                                       |          | 300         | °C   |  |

### Thermal Characteristics

| Symbol          | Parameter                                     |           | FQN1N50CTA | Unit |
|-----------------|---|-----------|------------|------|
| $R_{\theta JL}$ | Thermal Resistance, Junction-to-Lead, Max.    | (Note 5a) | 60         | °C/W |
| $R_{\thetaJA}$  | Thermal Resistance, Junction-to-Ambient, Max. | (Note 5b) | 140        | ·C/W |

December 2013

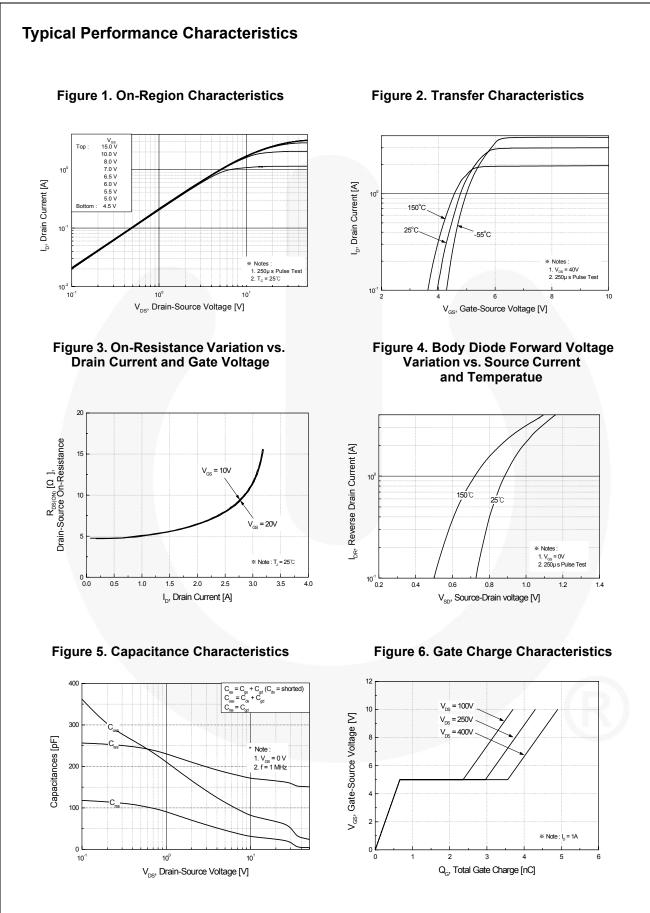
| Part Number                             |                     | Top Mark                           | Package             | ckage Packing Method Reel   |          | Size | Tape W | 'idth | Quantity   |  |
|---|---------------------|------------------------------------|---------------------|---|----------|------|--------|-------|------------|--|
| FQN1N                                   | I50CTA              | 1N50C                              | TO-92               | TO-92 AMMO N  |          | A    | N/A    |       | 2000 units |  |
| Electric                                | al Char             | racteristics T <sub>c</sub> = 25°C | unless otherwi      | se noted.   |          |      |        |       |            |  |
| Symbol                                  |                     | Parameter                          |                     | Test Conditions   |          | Min. | Тур.   | Max.  | Unit       |  |
| Off Charac                              | teristics           |                                    |                     |   |          |      |        |       |            |  |
| BV <sub>DSS</sub>                       | Drain-S             | ource Breakdown Voltage            | $V_{GS}$            | = 0 V, I <sub>D</sub> = 250 μA  |          | 500  |        |       | V          |  |
| ΔΒV <sub>DSS</sub><br>/ ΔΤ <sub>J</sub> | Breakdo<br>Coeffici | own Voltage Temperature<br>ent     | I <sub>D</sub> = 1  | $I_D = 250 \ \mu$ A, Referenced to 25°C   |          |      | 0.5    |       | V/°C       |  |
| I <sub>DSS</sub>                        | Zero Ga             | ate Voltage Drain Current          | $V_{DS}$            | = 500 V, V <sub>GS</sub> = 0 V  |          |      |        | 50    | μA         |  |
|   |                     |                                    | $V_{DS}$            | = 400 V, T <sub>C</sub> = 125°C   |          |      |        | 250   | μA         |  |
| I <sub>GSSF</sub>                       | Gate-Bo             | ody Leakage Current, Forwa         | ard V <sub>GS</sub> | = 30 V, V <sub>DS</sub> = 0 V   |          |      |        | 100   | nA         |  |
| I <sub>GSSR</sub>                       | Gate-Bo             | ody Leakage Current, Reve          | se V <sub>GS</sub>  | = -30 V, V <sub>DS</sub> = 0 V  |          |      |        | -100  | nA         |  |
| On Charac                               | teristics           |                                    |                     |   |          |      |        |       |            |  |
| V <sub>GS(th)</sub>                     | Gate Th             | nreshold Voltage                   | $V_{\text{DS}}$     | = V <sub>GS</sub> , I <sub>D</sub> = 250 μA   |          | 2.0  |        | 4.0   | V          |  |
| R <sub>DS(on)</sub>                     | Static D<br>On-Res  | rain-Source<br>istance             | V <sub>GS</sub>     | = 10 V, I <sub>D</sub> = 0.19 A   |          | -    | 4.6    | 6.0   | Ω          |  |
| 9 <sub>FS</sub>                         | Forward             | d Transconductance                 | $V_{DS}$            | = 40 V, I <sub>D</sub> = 0.19A  |          | \    | 0.6    |       | S          |  |
| Dynamic C                               | haracteristi        | ics                                |                     |   |          |      |        |       |            |  |
| C <sub>iss</sub>                        | Input Ca            | apacitance                         |                     | = 25 V, V <sub>GS</sub> = 0 V,  |          |      | 150    | 195   | pF         |  |
| C <sub>oss</sub>                        | Output              | Capacitance                        | f = 1               | f = 1.0 MHz   |          |      | 28     | 40    | pF         |  |
| C <sub>rss</sub>                        | Reverse             | e Transfer Capacitance             |                     |   |          |      | 4.1    |       | pF         |  |
| Switching                               | Characteris         | tics                               |                     |   |          |      |        |       |            |  |
| t <sub>d(on)</sub>                      | Turn-Or             | n Delay Time                       |                     | $V_{DD} = 250 \text{ V}, \text{ I}_{D} = 1.0 \text{ A},$ $R_{G} = 25 \Omega$        |          |      | 10     | 30    | ns         |  |
| r                                       | Turn-Or             | n Rise Time                        | R <sub>G</sub> =    |   |          |      | 10     | 30    | ns         |  |
| t <sub>d(off)</sub>                     | Turn-Of             | f Delay Time                       |                     |   |          |      | 20     | 50    | ns         |  |
| f                                       | Turn-Of             | f Fall Time                        |                     |   | (Note 4) |      | 15     | 40    | ns         |  |
| Qg                                      | Total Ga            | ate Charge                         | 20                  | $V_{DS} = 400 \text{ V}, \text{ I}_{D} = 1.0 \text{ A},$<br>$V_{GS} = 10 \text{ V}$ |          |      | 4.9    | 6.4   | nC         |  |
| Q <sub>gs</sub>                         | Gate-Se             | ource Charge                       | V <sub>GS</sub>     |   |          |      | 0.66   |       | nC         |  |
| Q <sub>gd</sub>                         | Gate-D              | rain Charge                        |                     |   | (Note 4) |      | 2.9    |       | nC         |  |
| Drain-Sour                              | ce Diode C          | haracteristics and Maximu          | m Ratings           |   |          |      |        |       |            |  |
| s                                       | Maximu              | m Continuous Drain-Source          | e Diode Forw        | vard Current  |          |      |        | 0.38  | А          |  |
| SM                                      | Maximu              | im Pulsed Drain-Source Dio         |                     | orward Current  |          |      |        | 3.04  | А          |  |
| V <sub>SD</sub>                         | Drain-S             | ource Diode Forward Voltag         |                     | $V_{GS}$ = 0 V, I <sub>S</sub> = 0.38 A   |          |      |        | 1.4   | V          |  |
| t <sub>rr</sub>                         | Reverse             | e Recovery Time                    |                     | = 0 V, I <sub>S</sub> = 1.0 A,  |          | -    | 188    |       | ns         |  |
| Q <sub>rr</sub>                         | Reverse             | e Recovery Charge                  | ai <sub>F</sub> /   | dt = 100 A/µs   |          |      | 0.55   |       | μC         |  |

2. L = 80 mH, I\_{AS} = 1.0 A, V\_{DD} = 50 V, R\_G = 25  $\Omega,$  starting  $\mbox{ T}_{J}$  = 25°C.

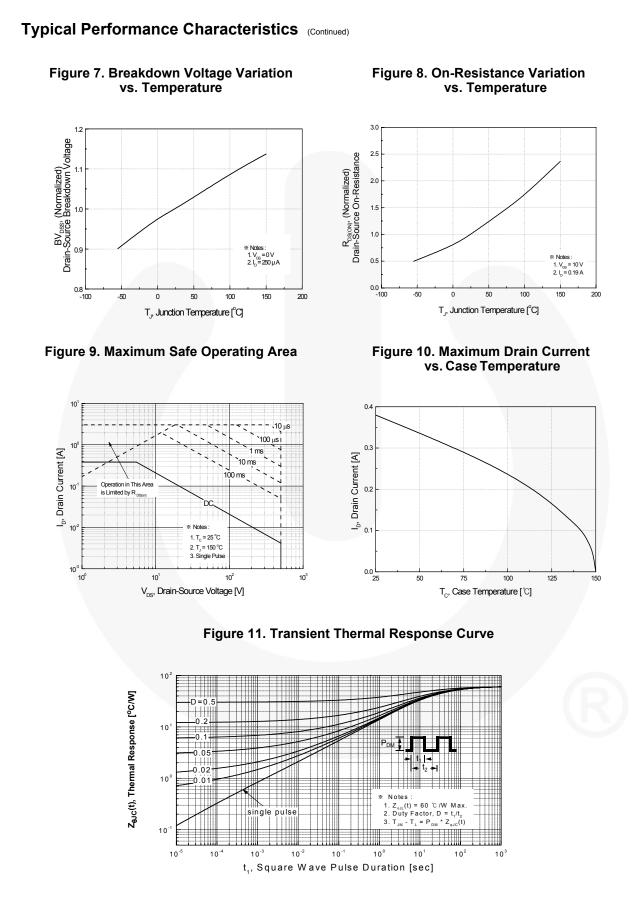
3. I\_{SD} \leq 0.38 A, di/dt  $\leq 200$  A/µs, V\_{DD}  $\leq BV_{DSS,}$  starting T\_J = 25°C.

4. Essentially independent of operating temperature.

FQN1N50C — N-Channel QFET® MOSFET



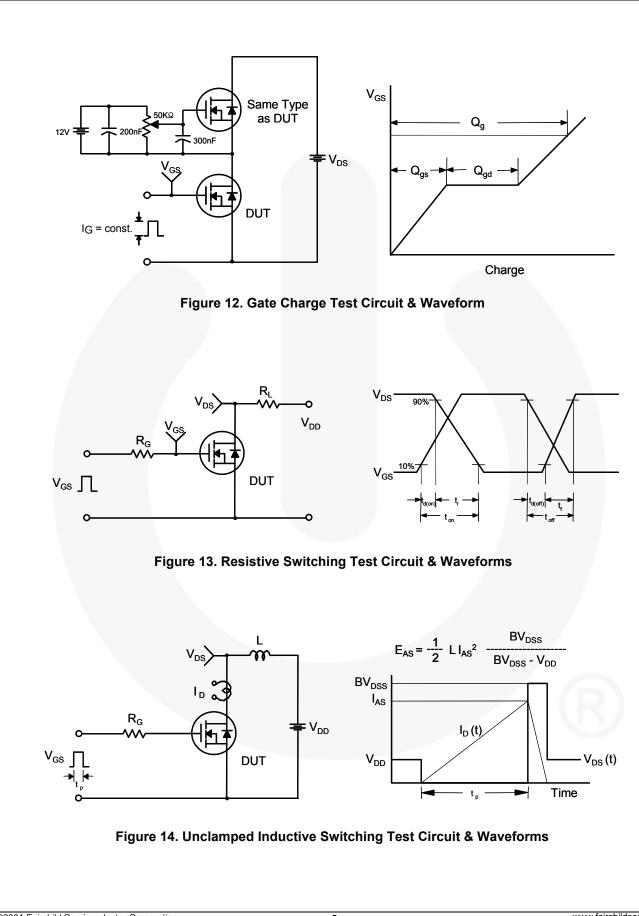
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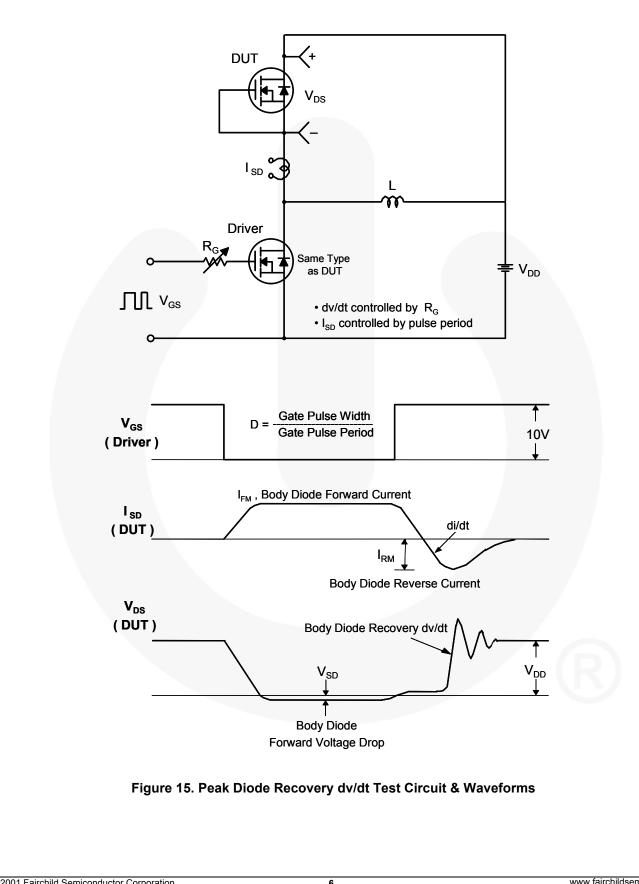
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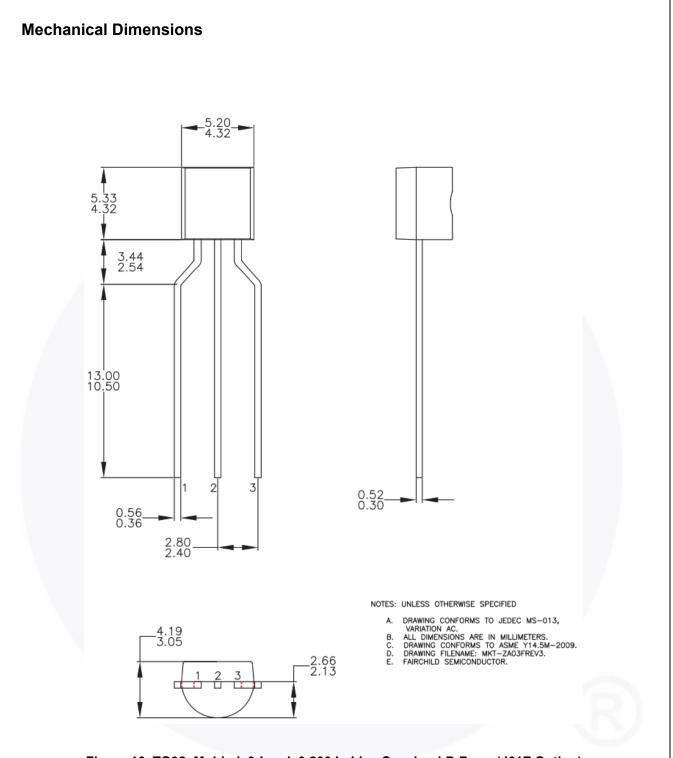
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FQN1N50C — N-Channel QFET<sup>®</sup> MOSFET



FQN1N50C — N-Channel QFET® MOSFET





#### Figure 16. TO92, Molded, 3-Lead, 0.200 In Line Spacing LD Form (J61Z Option)

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